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Lin

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[54] **IN SITU RESIST CONTROL DURING SPRAY AND SPIN IN VAPOR**

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[75] Inventor: **Burn J. Lin**, Austin, Tex.

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[73] Assignee: **International Business Machines Corporation**, Armonk, N.Y.

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[21] Appl. No.: **968,744**

Primary Examiner—Janyce Bell

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Attorney, Agent, or Firm—Graham S. Jones, II; Dale M. Crockatt

[51] Int. Cl.⁵ **B05D 3/12**

[57] **ABSTRACT**

[52] U.S. Cl. **427/9; 427/10; 427/240; 427/325; 427/385.5; 118/52; 118/668**

Spin coating of resist on a semiconductor wafer is done in a controlled chamber, starting with introducing a resist solvent vapor into the chamber from a nozzle, applying the resist by spraying a very thin layer of the resist material, monitoring and adjusting the resist thickness during spinning in vapor, and then removing solvent from the chamber. The result is a saving in resist material and enhanced coating uniformity.

[58] Field of Search **427/240, 9, 385.5, 10, 427/325; 118/668, 52**

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30 Claims, 2 Drawing Sheets

